

N-Channel Enhancement Mode
Low Q_g
Surface Mount Package
Nanosecond Switching

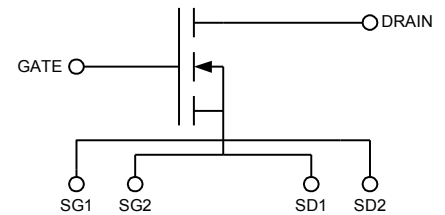
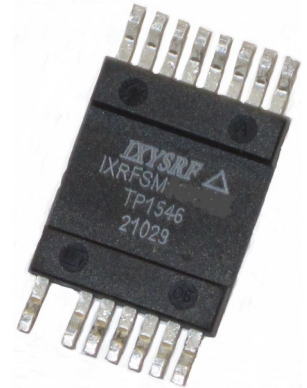
Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_c = 25^\circ\text{C}$	12	A
I_{DM}	$T_c = 25^\circ\text{C}$, pulse width limited by T_{JM}	72	A
I_{AR}	$T_c = 25^\circ\text{C}$	12	A
E_{AR}	$T_c = 25^\circ\text{C}$	30	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 0.2\Omega$	5	V/ns
	$I_S = 0$	>200	V/ns
P_{DC}		940	W
P_{DHS}	$T_c = 25^\circ\text{C}$ Derate $3.7\text{W}/^\circ\text{C}$ above 25°C	425	W
P_{DAMB}	$T_c = 25^\circ\text{C}$	4.5	W

$$V_{DSS} = 1000\text{ V}$$

$$I_{D25} = 12\text{ A}$$

$$R_{DS(on)} \leq 1.05\ \Omega$$

$$P_{DC} = 900\text{ W}$$



Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
$T_J = 25^\circ\text{C}$ unless otherwise specified				
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 3\text{ ma}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{a}$	4.0	4.7	5.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = 0.8\text{ V}_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0$, $T_J = 125^\circ\text{C}$			50 μA
				1 mA
$R_{DS(on)}$	$V_{GS} = 15\text{ V}$, $I_D = 0.5I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.05 Ω
R_{thJC}				0.14 $^\circ\text{C}/\text{W}$
R_{thJHS}			0.34	$^\circ\text{C}/\text{W}$
g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 0.5I_{D25}$, pulse test		6.7	8.0 S
T_J		-55		+150 $^\circ\text{C}$
T_{JM}			150	$^\circ\text{C}$
T_{stg}		-55		+150 $^\circ\text{C}$
T_L	1.6mm (0.062 in) from case for 10 s		300	$^\circ\text{C}$
Weight			5	g

Features

- Isolated Substrate
 - High isolation voltage (>2500V)
 - Excellent thermal transfer
 - Increased temperature and power cycling capability
- IXYS advanced low Q_g process
- Low gate charge and capacitances
 - Easier to drive
 - Faster switching
- Low $R_{DS(on)}$
- Very low insertion inductance (<2nH)
- No beryllium oxide (BeO) or other hazardous materials

Advantages

- Optimized for RF and high speed switching
- Easy to mount—no insulators needed
- High power density

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
(T _J = 25°C unless otherwise specified)				
R_G			0.3	Ω
C_{iss}		2125	2500	2875 pF
C_{oss}	V _{GS} = 0 V, V _{DS} = 0.8 V _{DSS(max)} , f = 1 MHz	93	110	127 pF
C_{rss}		20	25	30 pF
C_{stray}	Back Metal to any Pin		33	pF
T_{d(on)}			5	ns
T_{on}	V _{GS} = 15 V, V _{DS} = 0.8 V _{DSS} I _D = 0.5 I _{DM}		3	ns
T_{d(off)}	R _G = 0.2 Ω (External)		5	ns
T_{off}			8	ns
Q_{g(on)}			77	nC
Q_{gs}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} I _D = 0.5 I _{D25}		16	nC
Q_{gd}			42	nC

Source-Drain Diode		Characteristic Values		
(T _J = 25°C unless otherwise specified)				
Symbol	Test Conditions	min.	typ.	max.
I_S	V _{GS} = 0 V			12 A
I_{SM}	Repetitive; pulse width limited by T _{JM}			72 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2%			1.5 V
T_{rr}			200	ns
Q_{RM}	I _F = I _S , -di/dt = 100A/μs, V _R = 100V		0.6	μC
I_{RM}			7	A

CAUTION: Operation at or above the Maximum Ratings values may impact device reliability or cause permanent damage to the device.

Information in this document is believed to be accurate and reliable. IXYSRF reserves the right to make changes to information published in this document at any time and without notice.

Fig. 1

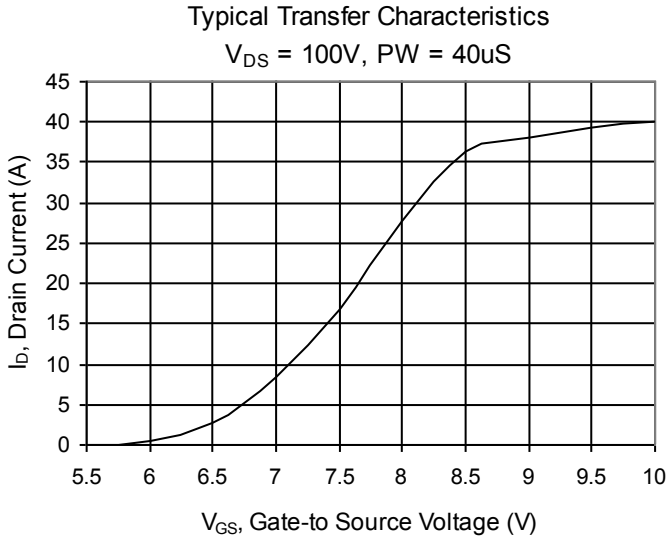


Fig. 2

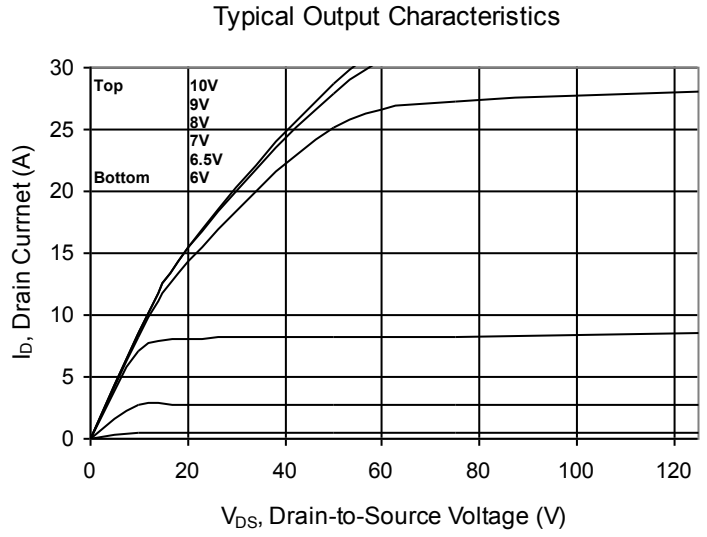


Fig. 3 Gate Charge vs. Gate-to-Source Voltage

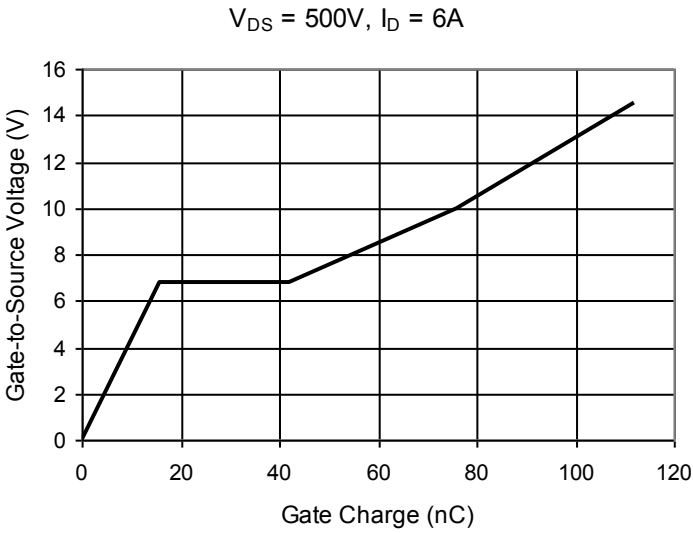


Fig. 4

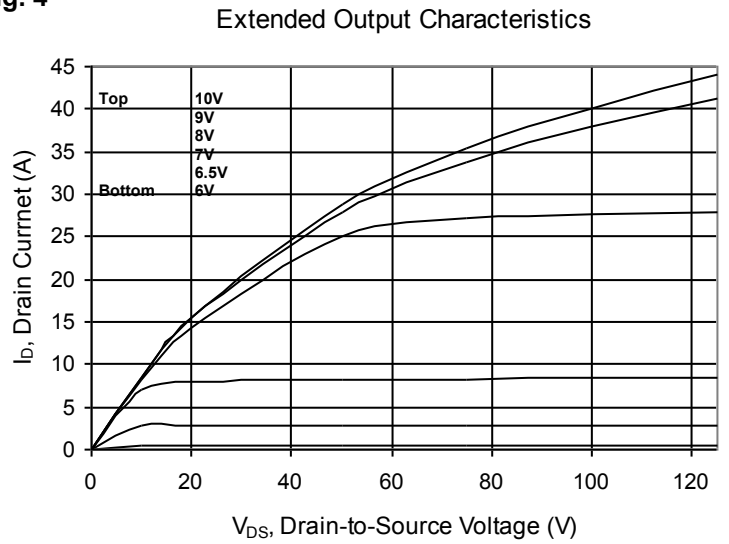


Fig. 5

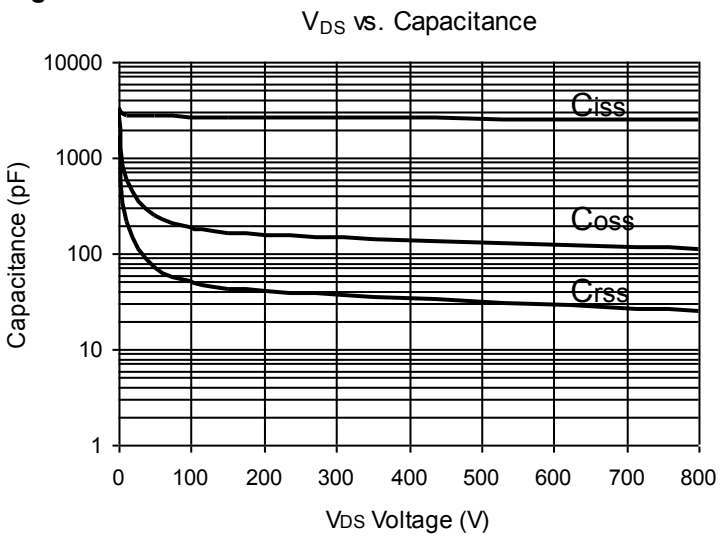


Fig. 6

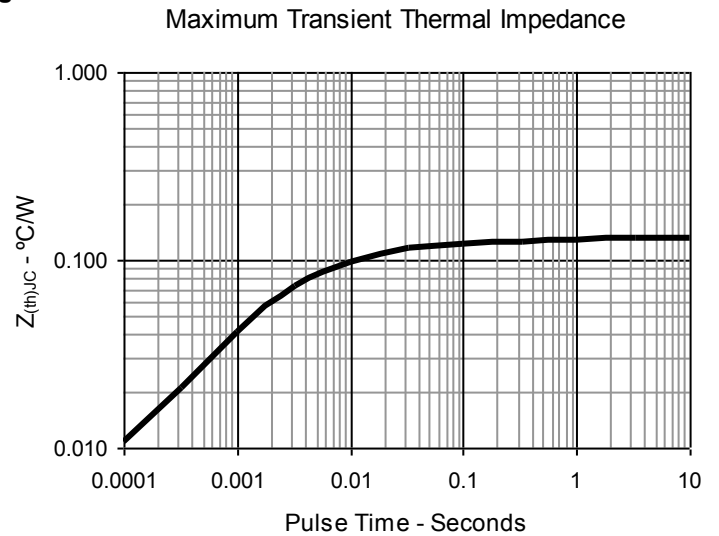


Fig. 7

Typical Transfer Characteristics
 $V_{DD} = 25V$, P.W. = $10\mu S$

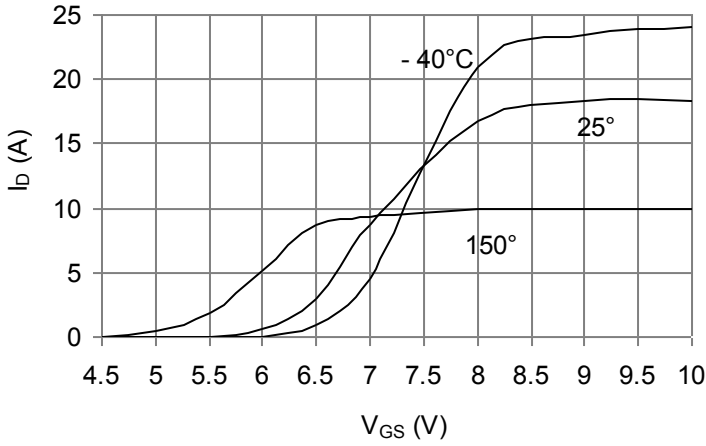


Fig. 8

Normalized $V_{GS(th)}$ vs. Temperature
 $I_D = 50mA$, $V_{GS} = V_{DD}$

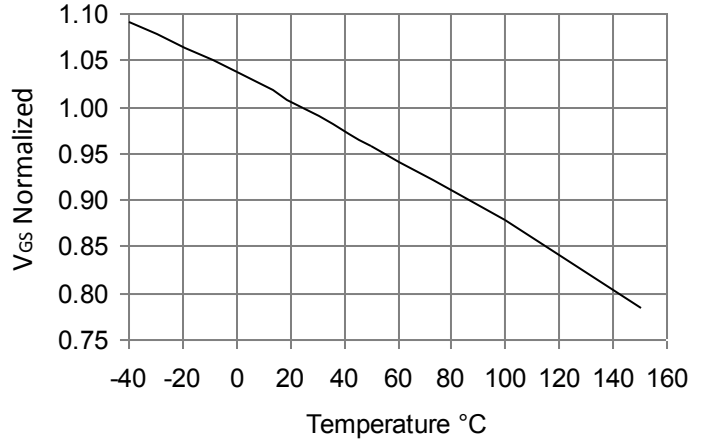


Fig. 9

$R_{DS(ON)}$ vs. Drain Current
 $V_{GS} = 10V$, PW = $10\mu S$

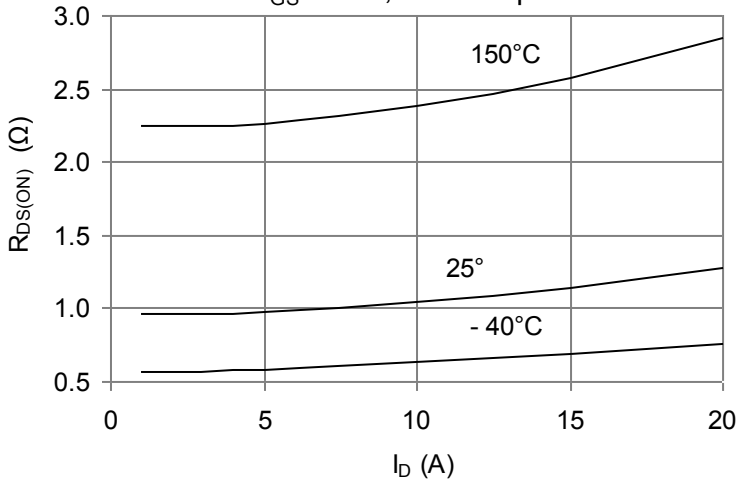


Fig. 10

Normalized $R_{DS(ON)}$ vs. Temperature
 $V_{GS} = 10V$, $I_D = 6A$, PW = $10\mu S$

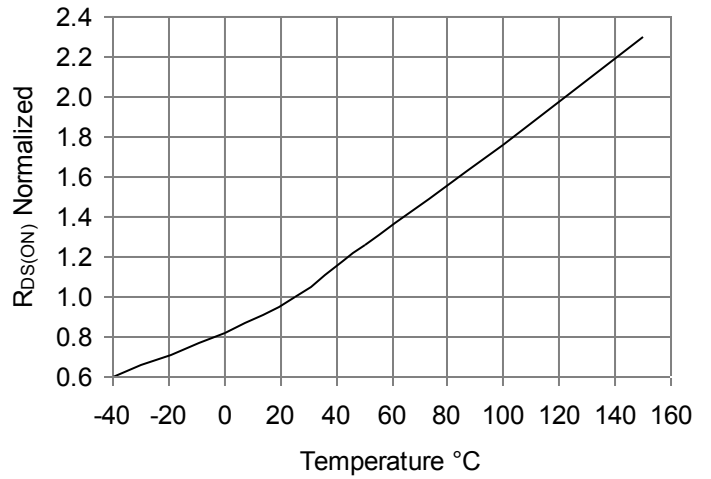
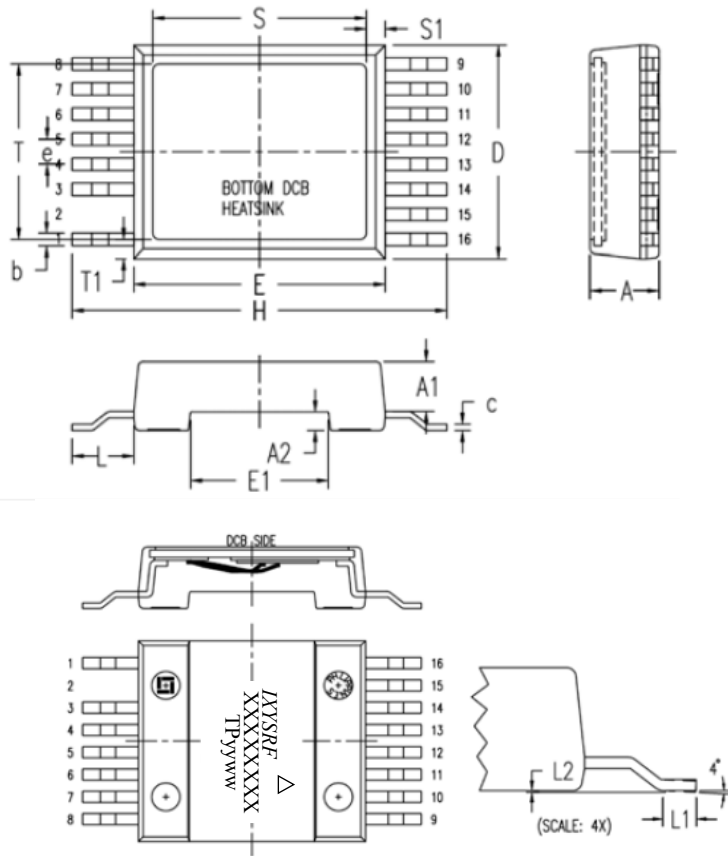


Fig. 11 Pin Description

Symbol	Function	Pin Number	Description
SG1	Source-gate side	1, 3	Source connection on gate side
SG2	Source-gate side	6, 7, 8	Source connection on gate side
SD1	Source-drain side	9, 10	Source connection on drain side
SD2	Source-drain side	15, 16	Source connection on drain side
Drain	Drain	11, 12, 13, 14	MOSFET Drain
Gate	Gate	4, 5	MOSFET Gate

Fig. 12 Package Description



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.209	.224	5.30	5.70
A1	.154	.161	3.90	4.10
A2	.055	.063	1.40	1.60
b	.035	.045	0.90	1.15
c	.018	.026	0.45	0.65
D	.661	.677	16.80	17.20
E	.780	.795	19.80	20.20
E1	.425	.441	10.80	11.20
e	.079 BSC		2.00 BSC	
H	1.161	1.185	29.50	30.10
L	.181	.209	4.60	5.30
L1	.051	.067	1.30	1.70
L2	.000	.006	0.00	0.15
S	.661	.677	16.80	17.20
S1	.051	.067	1.30	1.70
T	.543	.559	13.80	14.20
T1	.051	.067	1.30	1.70

Note:

1. ALL LEADS ARE PURE MATTE TIN PLATED.
2. Cu SURFACE OF BOTTOM DCB IS PRE-Ni PLATED UNLESS OTHERWISE STATED
3. Cu SURFACE OF BOTTOM DCB IS ELECTRICALLY ISOLATED 2,500V AC FROM ALL OTHER LEADS.
4. PIN 2 N/A, missing, used for device orientation.

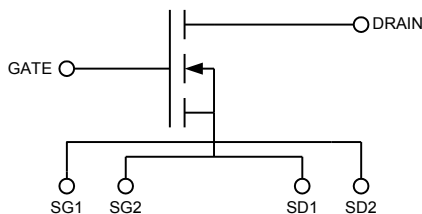
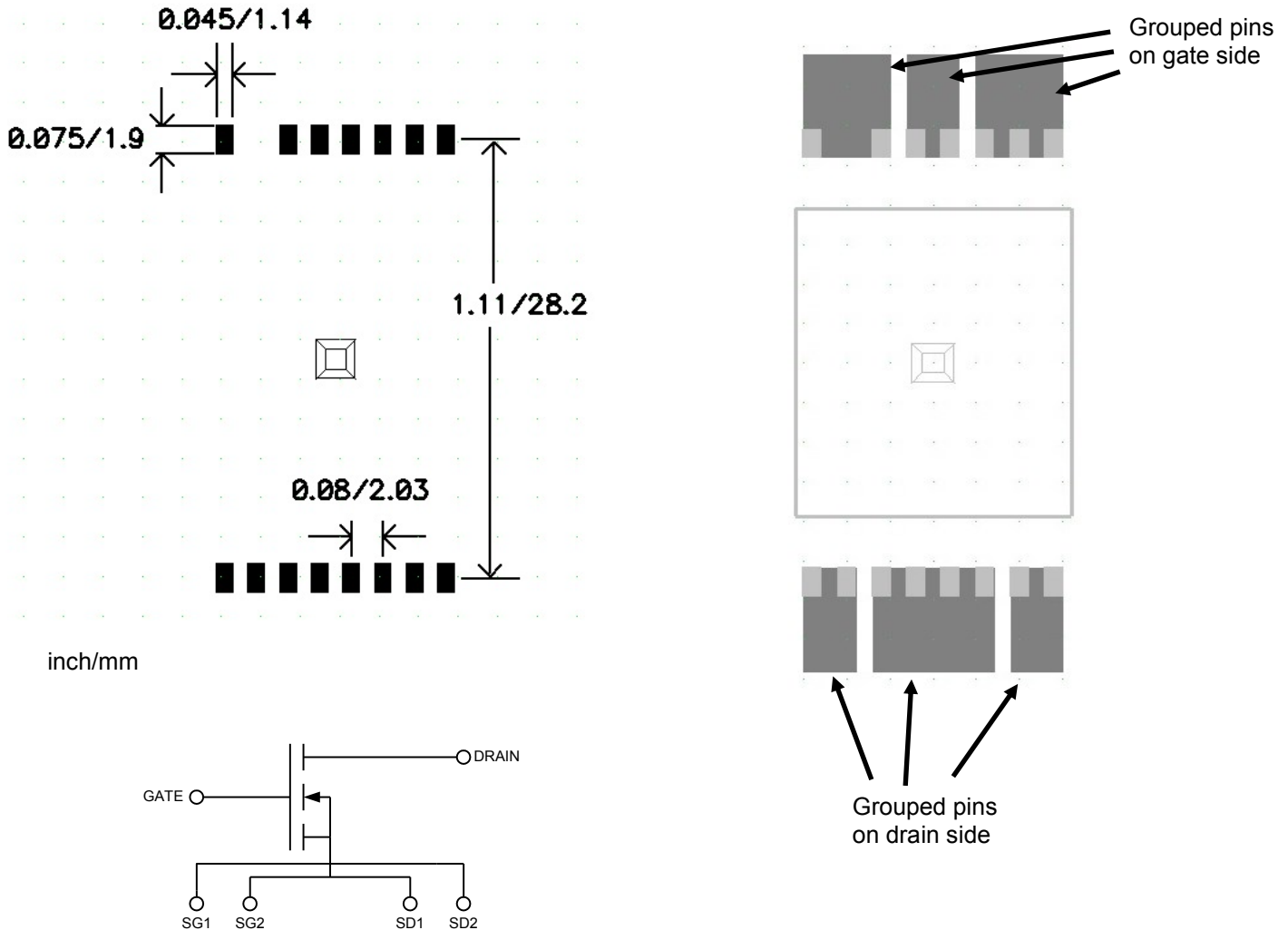


Fig. 13 Footprint and PCB layout

For optimum results, multiple pins of the same type should be grouped together on the PCB as shown below. This assures wide traces to the attached driver and load, minimizing parasitic inductance. The source pin groups, SG1, SG2, SD1, SD2, are all source connections at the die. For best operation, the source groups would be ideally incorporated into a large contiguous ground plane on the same side of mounting on the circuit board. In other words, instead of routing ground traces to the device during layout, the footprint would be set over a large ground plane with drain and gate traces routed out of the ground plane. This is done during layout by first establishing a polygon that covers the entire PCB, representing the ground plane, and that is 'poured' around needed traces by the layout software.



Doc # ds IXRFSM12N100 Rev. 02/20
© 2016 IXYS RF

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [RF MOSFET Transistors](#) category:

Click to view products by [IXYS](#) manufacturer:

Other Similar products are found below :

[MRF166W](#) [MHT1006NT1](#) [FH2164](#) [MRFE8VP8600HR5](#) [BLF245](#) [BLF278](#) [ARF1511](#) [ARF465BG](#) [BF 2030 E6814](#) [BLF861A](#) [3SK263-5-TG-E](#) [VRF154FL](#) [MRF150J](#) [MRF6S20010GNR1](#) [DU1215S](#) [DU28200M](#) [VRF150MP](#) [MMRF1015NR1](#) [MRF154](#) [MRF175LU](#)
[MRF6S20010GNR1](#) [UF28100M](#) [MW6S010GNR1](#) [MW6S010GNR1](#) [DU2820S](#) [SD2943W](#) [SD2932BW](#) [SD2941-10W](#) [MRF24301HR5](#)
[ARF469AG](#) [ARF463BP1G](#) [MHT1008NT1](#) [MMRF1014NT1](#) [MRF426](#) [MRF422](#) [BLW96](#) [ARF468AG](#) [VRF161MP](#) [ARF468BG](#)
[MRFE6VP61K25NR6](#) [MRFE6VP5300NR1](#) [A2T27S020NR1](#) [MMRF1304NR1](#) [MRFE6S9060GNR1](#) [MMRF1008GHR5](#) [A2T27S007NT1](#)
[AFT09MP055NR1](#) [DU2860U](#) [MHT1803A](#) [D2081UK.F](#)